

EO-532-Subnano/1~500μJ/1~1400mW

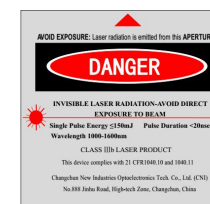
**HIGH ENERGY DIODE
PUMPED ALL-SOLID-STATE
Q-SWITCHED LASER**

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in biomedicine, environmental monitoring, scientific research, and so on.

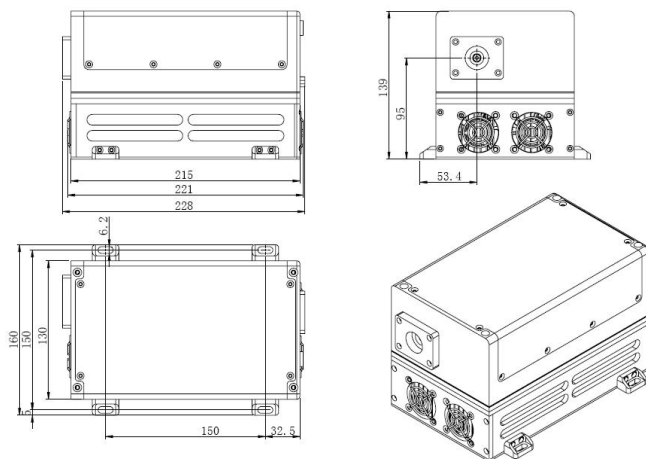


SPECIFICATIONS

Wavelength (nm)	532±1nm	
Operating mode	Q-switched: EO (Electro-optic)	
Single pulse energy (uJ)	300uJ@1KHz	500uJ@1KHz
Output power (mW)	1400mW@10KHz	500mW@1KHz
Power stability	<3% , <5%	
Pulse duration (ns)	<1.5ns@1KHz	
Rep. rate (kHz)	1KHz~10KHz	
Beam diameter (mm)	~1mm	
Beam height from base plate (mm)	95	
Beam divergence, full angle (mrad)	<3mrad	
Cooled method	Air cooled	
Warm-up time (minutes)	<15	
Power supply	AC 220V/DC 24V	
Operating temperature (°C)	15~30	
Expected lifetime (hours)	10000h	
Warranty period	1 year	

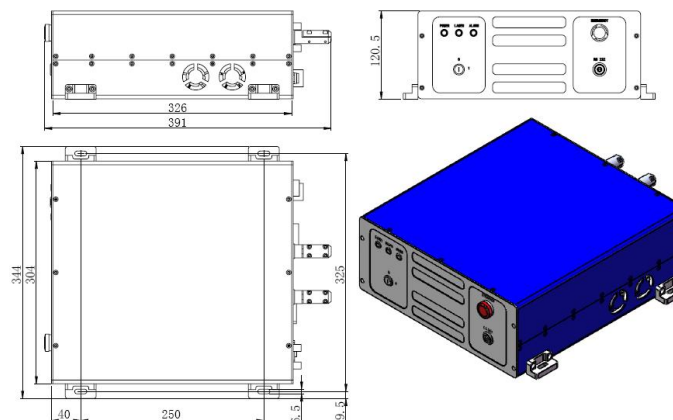


EO-532-Subnano



228(L)×160(W)×139(H)mm³ 7kg

PSU-EO-Subnano



391(L)×344(W)×120.5(H)mm³ 10kg